

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3857	((438/510) or (438/514) or (438/542) or (438/389) or (438/390) or (438/238) or (438/246-247) or (438/249)).CCLS.	US-PGPUB; USPAT	OR	OFF	2010/09/03 21:29
L2	1027	1 and (trench with (silicon or polysilicon or poly-si or "Si"))	US-PGPUB; USPAT	OR	ON	2010/09/03 21:29
L3	650	@ad <= "20040128" and 2	US-PGPUB; USPAT	OR	OFF	2010/09/03 21:29
L4	3	3 and ((silicon or polysilicon or poly-si or "Si") with ((gas adj phase) or ("AsH.sub.3" or AsH\$2 or "AS.sub"\$4)) with dop\$4 with concentration)	US-PGPUB; USPAT	OR	ON	2010/09/03 21:29
S1	1	10/766,053	US-PGPUB; USPAT	OR	ON	2009/09/23 00:40
S2	41238	trench with (silicon or polysilicon or poly-si or "Si")	US-PGPUB; USPAT	OR	ON	2009/09/23 00:46
S3	149430	(silicon or polysilicon or poly-si or "Si") with (implant\$3 or dop\$3)	US-PGPUB; USPAT	OR	ON	2009/09/23 00:47
S4	25680	S2 and S3	US-PGPUB; USPAT	OR	ON	2009/09/23 00:47
S5	26731	(silicon or polysilicon or poly-si or "Si") with (implant\$3 or dop\$3) with (dose or concentration)	US-PGPUB; USPAT	OR	ON	2009/09/23 00:48
S6	5694	S4 and S5	US-PGPUB; USPAT	OR	ON	2009/09/23 00:48
S7	1	("6759335").PN.	US-PGPUB; USPAT	OR	OFF	2009/09/23 00:48

S8	389	S6 and precursor	US- PGPUB; USPAT	OR	ON	2009/09/23 00:50
S9	216	S8 and ((temperature or heat\$3) with (dop\$3 or implant\$3))	US- PGPUB; USPAT	OR	ON	2009/09/23 00:51
S10	147	S9 and (dop\$3 or implant\$3) with (arsenic or phosphorous)	US- PGPUB; USPAT	OR	ON	2009/09/23 00:53
S11	41552	trench with (silicon or polysilicon or poly-si or "Si")	US- PGPUB; USPAT	OR	ON	2009/10/20 18:46
S12	150473	(silicon or polysilicon or poly-si or "Si") with (implant\$3 or dop\$3)	US- PGPUB; USPAT	OR	ON	2009/10/20 18:46
S13	25874	S11 and S12	US- PGPUB; USPAT	OR	ON	2009/10/20 18:46
S14	26893	(silicon or polysilicon or poly-si or "Si") with (implant\$3 or dop\$3) with (dose or concentration)	US- PGPUB; USPAT	OR	ON	2009/10/20 18:46
S15	5734	S13 and S14	US- PGPUB; USPAT	OR	ON	2009/10/20 18:46
S16	393	S15 and precursor	US- PGPUB; USPAT	OR	ON	2009/10/20 18:46
S17	218	S16 and ((temperature or heat\$3) with (dop\$3 or implant\$3))	US- PGPUB; USPAT	OR	ON	2009/10/20 18:46
S18	147	S17 and (dop\$3 or implant\$3) with (arsenic or phosphorous)	US- PGPUB; USPAT	OR	ON	2009/10/20 18:46
S19	71	@ad <= "20040128" and S18	US- PGPUB; USPAT	OR	OFF	2009/10/20 18:46
S20	1	("20040084149").PN.	US- PGPUB; USPAT	OR	OFF	2009/10/20 19:48
S21	82	(silicon or polysilicon or poly-si or "Si") with ((gas adj phase) or ("AsH. sub.3" or AsH\$2 or "AS. sub"\$4)) with dop\$4 with concentration	US- PGPUB; USPAT	OR	ON	2010/09/03 02:14

S22	56	@ad <= "20040128" and S21	US-PGPUB; USPAT	OR	OFF	2010/09/03 02:15
S23	1	("20020024091").PN.	US-PGPUB; USPAT	OR	OFF	2010/09/03 02:30
S24	1	("20030207532").PN.	US-PGPUB; USPAT	OR	OFF	2010/09/03 02:58
S25	1	("6759335").PN.	US-PGPUB; USPAT	OR	OFF	2010/09/03 18:15
S26	10	((wet adj process) or (wet adj clean)) with substrate with (benefit or advantage)	US-PGPUB; USPAT	OR	OFF	2010/09/03 20:06
S27	0	((wet adj process) or (wet adj clean)) with trench with (benefit or advantage)	US-PGPUB; USPAT	OR	OFF	2010/09/03 20:12
S28	199	((wet adj process) or (wet adj clean)) with (benefit or advantage)	US-PGPUB; USPAT	OR	OFF	2010/09/03 20:12

9/ 3/ 10 9:31:30 PM

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